



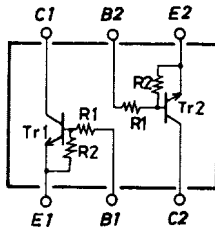
FC132

NPN Epitaxial Planar Silicon Composite Transistor Switching Applications (with Bias Resistance)

Features

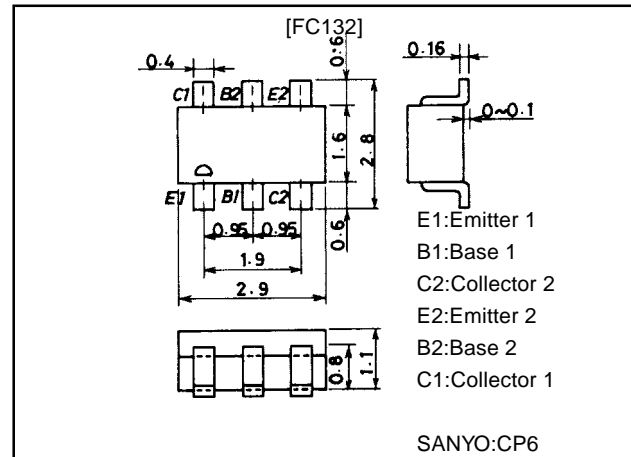
- On-chip bias resistances (R1=10kΩ, R2=47kΩ).
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC132 is formed with two chips, being equivalent to the 2SC4047, placed in one package.
- Excellent in thermal equilibrium and pair capability.

Electrical Connection



Package Dimensions

unit:mm
2067



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		50	V
Collector-to-Emitter Voltage	V _{CEO}		50	V
Emitter-to-Base Voltage	V _{EBO}		6	V
Collector Current	I _C		100	mA
Peak Collector Current	I _{CP}		200	mA
Collector Dissipation	P _C	1 unit	200	mW
Total Power Dissipation	P _T		300	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

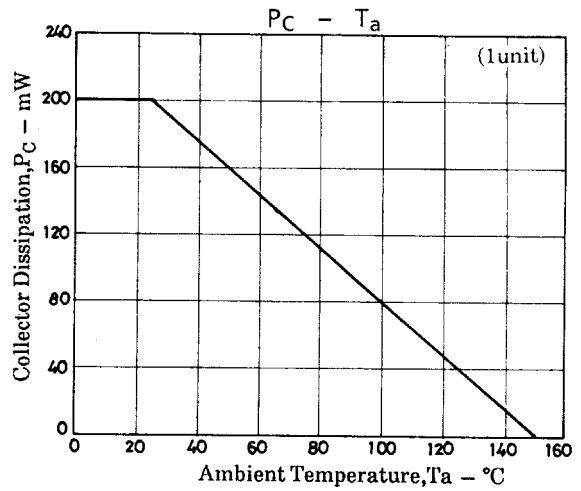
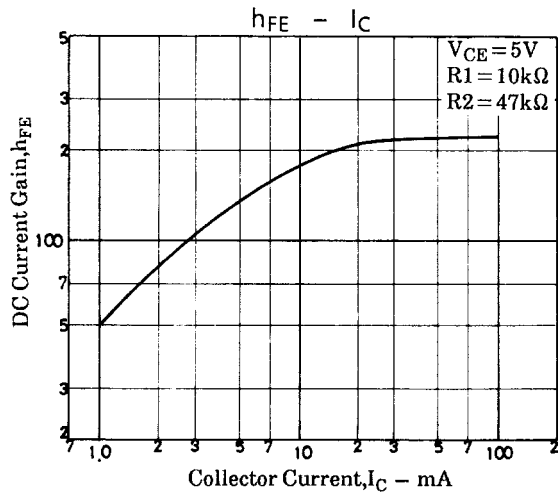
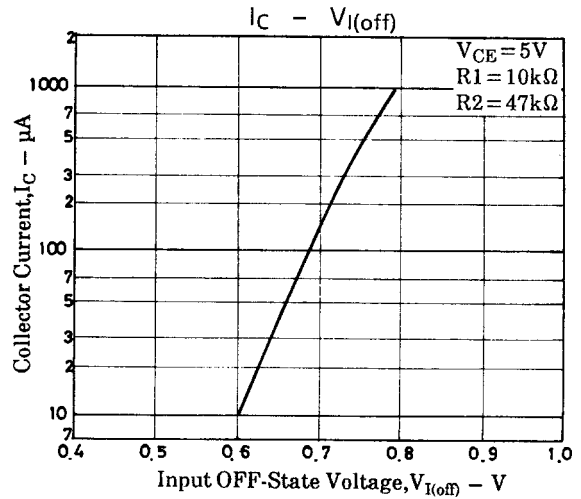
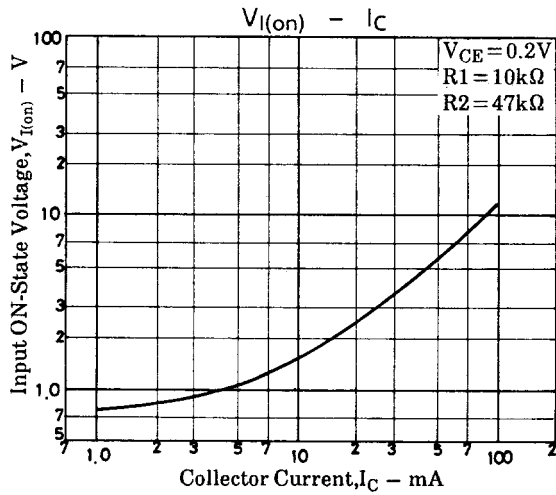
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CB0}	V _{CB} =40V, I _E =0			0.1	μA
Collector Cutoff Current	I _{CEO}	V _{CB} =40V, I _E =0			0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0	67	88	125	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =5mA	70			
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =5mA		250		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		3.3		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA		0.1	0.3	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	50			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =100μA, R _{BE} =∞	50			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} =5V, I _C =100μA	0.5	0.7	0.9	V
Input ON-State Voltage	V _{I(on)}	V _{CE} =0.2V, I _C =5mA	0.7	1.0	2.0	V
Input Resistance	R ₁		7	10	13	kΩ
Resistancnce Ratio	R _{1/R2}		0.193	0.213	0.234	

Note:The specifications shown above are for each individual transistor.

Marking:132

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